



Application Number

10 | 688,047

"Chung Foong Tan et al.

10/17/03

Group Art Unit

O I P E INFO  
 JAN 29 2004 JCS6  
 CENTRAL  
 CENTRAL

(Use several sheets if necessary)

[illegible][illegible]

MG	-	"Effects of end-of-range dislocation loops on transient enhanced diffusion of indium implanted in silicon", T. Noda et al., <u>Journal of Applied Physics</u> , Vol. 88, No. 9, Nov. 2001, pp. 4980-4984.
MG	-	"Enhanced electrical activation of indium coimplanted with carbon in a silicon substrate," H. Boudinov et al., <u>Journal of Applied Physics</u> , Vol. 86, No. 10, pp. 5909-5911, Nov. 15, 1999.

DATE CONSIDERED

Maria Guerrero

4-12-05

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

**BEST AVAILABLE COPY**



Application Number

10/688,047

Chung Foong Tan et al.

10/17/03

Group Art Unit

[illegible][illegible]

MG	-	"Elimination of secondary defects in preamorphized Si by C <sup>+</sup> implantation", Satoshi Mishikawa et al., <u>Applied Physics Letters</u> , 62(3), Jan. 18, 1993, pp. 303-305.
MG	-	"Removal of end of range defect in Ge <sup>+</sup> pre-amorphized Si by carbon ion implantation", Pang-Shiu Chen et al., <u>Jrnl of Applied Physics</u> , Vol. 85, No. 6, March 15, 1999, pp. 3114-3119.
EXAMINER		DATE CONSIDERED
Yuan Guenero		4-12-05

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.